



CT3H4 Series

4-Pin Half Pitch Mini-Flat Phototransistor

Features

- High isolation 3750 V_{RMS}
- Multiple CTR selection available
- DC input with transistor output
- Operating temperature range - 55 °C to 125 °C
- RoHS compliance
- REACH compliance
- Halogen compliance
- Regulatory Approvals
 - UL - UL1577 (Pending Approval)
 - VDE - EN60747-5-5 (Pending Approval)
 - CQC – GB4943.1, GB8898 (Pending Approval)
 - IEC60065, IEC60950 (Pending Approval)

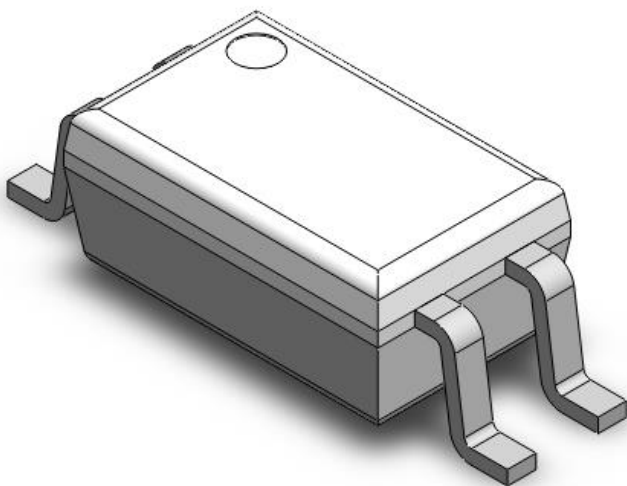
Description

The CT3H4 series consists of a phototransistor optically coupled to two gallium arsenide Infrared-emitting diode, connected in inverse parallel in a 4-lead half pitch Mini-Flat package.

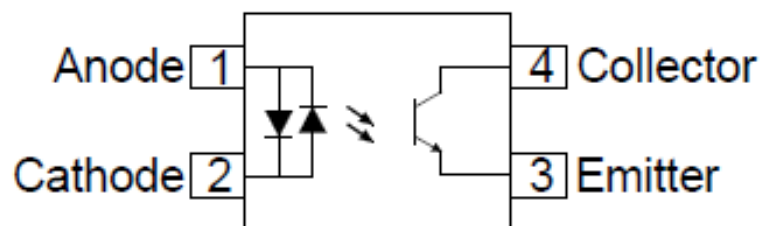
Applications

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Package Outline



Schematic



CT3H4



CT3H4 Series 4-Pin Half Pitch Mini-Flat Phototransistor

Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
V _{ISO}	Isolation voltage	3750	V _{RMS}	
P _{TOT}	Total power dissipation	200	mW	
T _{OPR}	Operating temperature	-55 ~ +125	°C	
T _{STG}	Storage temperature	-55 ~ +150	°C	
T _{SOL}	Soldering temperature	260	°C	
Emitter				
I _F	Forward current	60	mA	
I _{F(TRANS)}	Peak transient current (≤1μs P.W,300pps)	1000	mA	
V _R	Reverse voltage	6	V	
P _D	Emitter power dissipation	70	mW	
Detector				
P _C	Detector power dissipation	150	mW	
B _{VCEO}	Collector-Emitter Breakdown Voltage	80	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	7	V	
I _C	Collector Current	50	mA	



Electrical Characteristics $T_A = 25^\circ\text{C}$ (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V_F	Forward voltage	$I_F = \pm 20\text{mA}$	-	1.2	1.4	V	
C_{IN}	Input Capacitance	$f = 1\text{MHz}$	-	10	30	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown	$I_C = 100\mu\text{A}$	80	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown	$I_E = 100\mu\text{A}$	7	-	-	V	
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$	-	-	100	nA	

Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes	
CTR	Current Transfer Ratio	$I_F = \pm 1\text{mA}, V_{CE} = 5\text{V}$	CT3H4	20		300	%	
			CT3H4A	50		150		
			CT3H4B	100		300		
	CTR Symmetry	$I_F = \pm 1\text{mA}, V_{CE} = 5\text{V}$	0.5		2.0			
$V_{CE(SAT)}$	Collector -Emitter Saturation Voltage	$I_F = \pm 20\text{mA}, I_C = 1\text{mA}$	-	0.1	0.2	V		
R_{IO}	Isolation Resistance	$V_{IO} = 500\text{V}_{DC}$	5×10^{10}	-	-	Ω		
C_{IO}	Isolation Capacitance	$f = 1\text{MHz}$	-	0.25	1	pF		

Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
t_r	Rise Time	$I_C = 2\text{mA}, V_{CE} = 2\text{V}$ $R_L = 100\Omega$	-	5	16	μs	
t_f	Fall Time		-	6	16		
t_{on}	Turn-on time		8	20	μs		
t_{off}	Turn-off time		7	20			



Typical Characteristic Curves

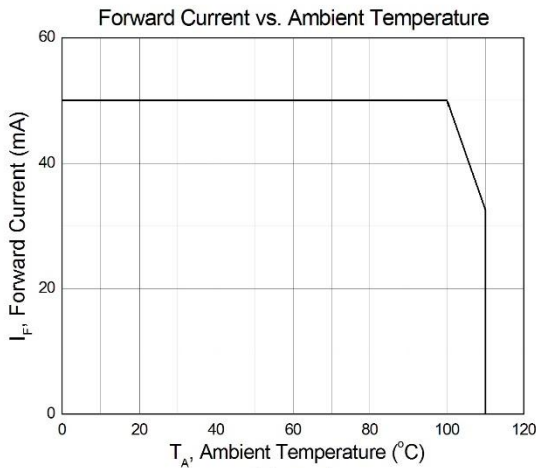


Figure 1

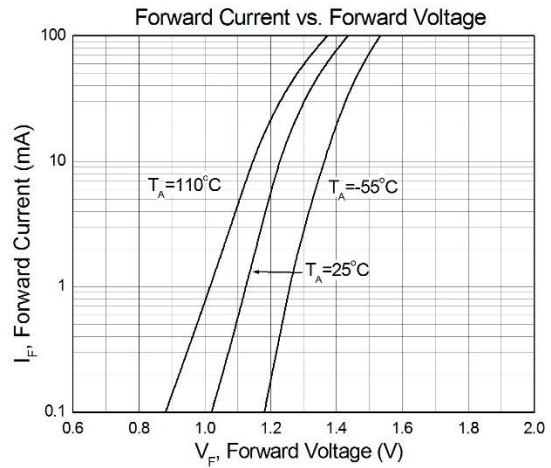


Figure 2

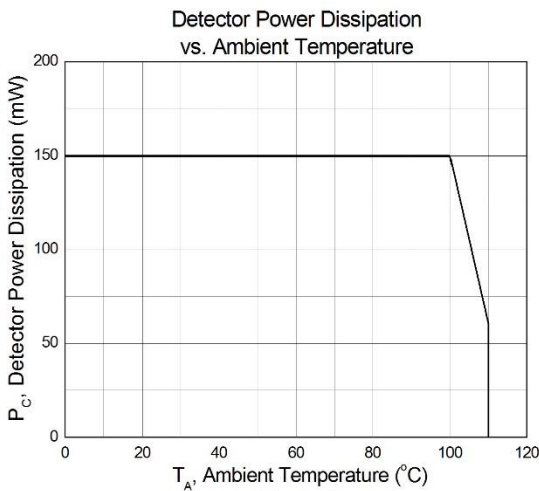


Figure 3

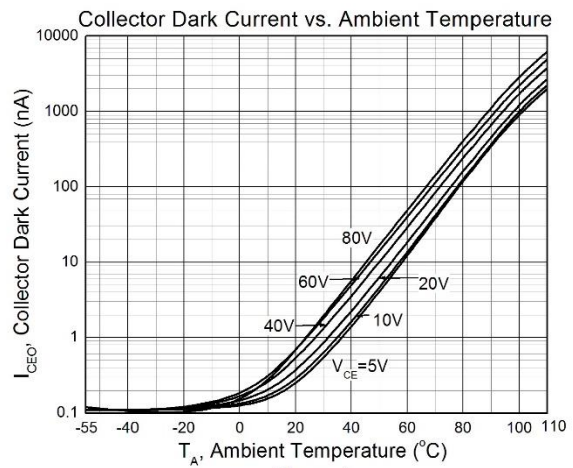


Figure 4

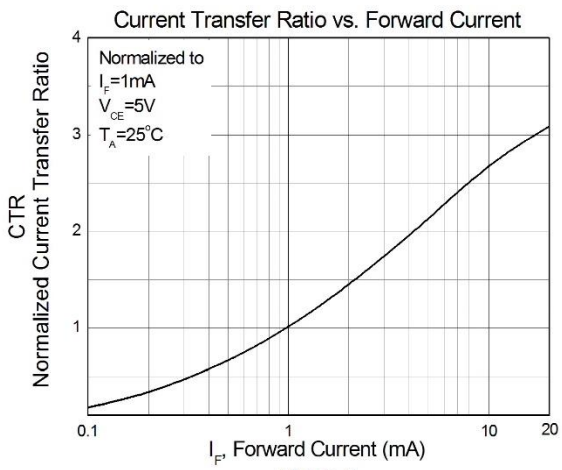


Figure 5

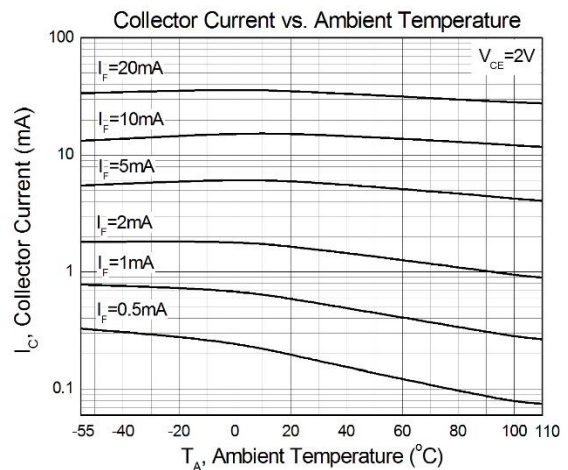


Figure 6



4-Pin Half Pitch Mini-Flat Phototransistor

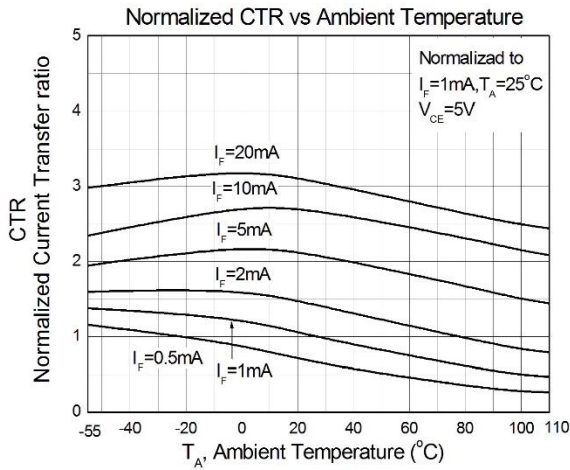


Figure 7

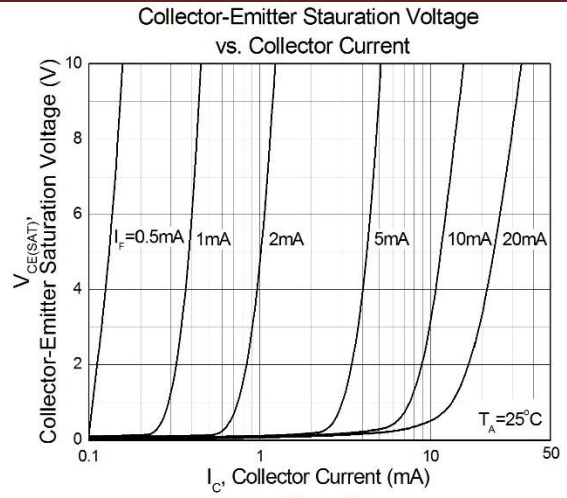


Figure 8

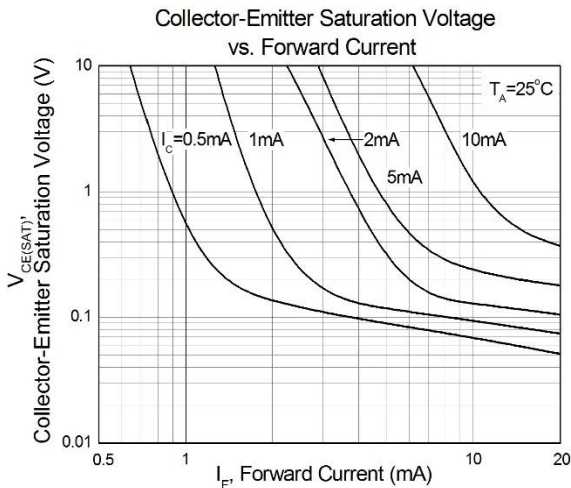


Figure 9

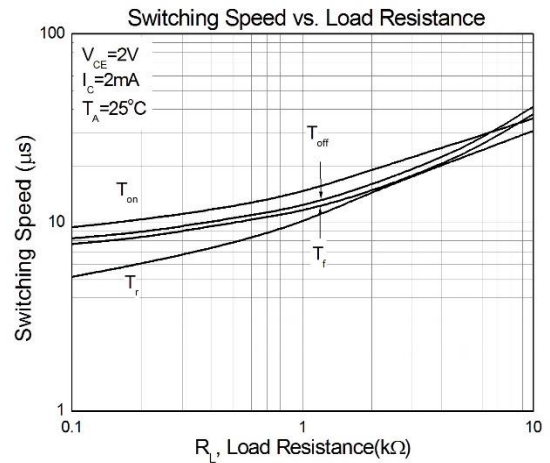


Figure 10

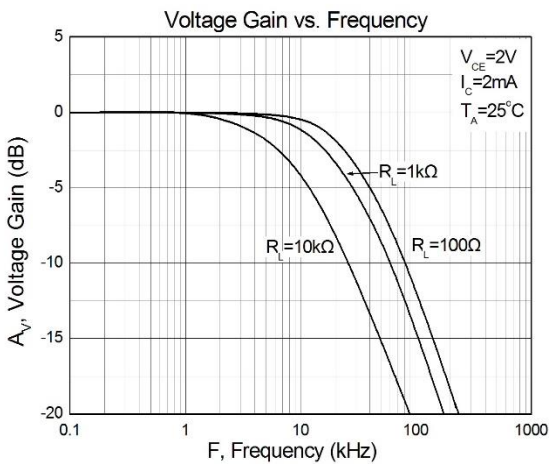


Figure 11

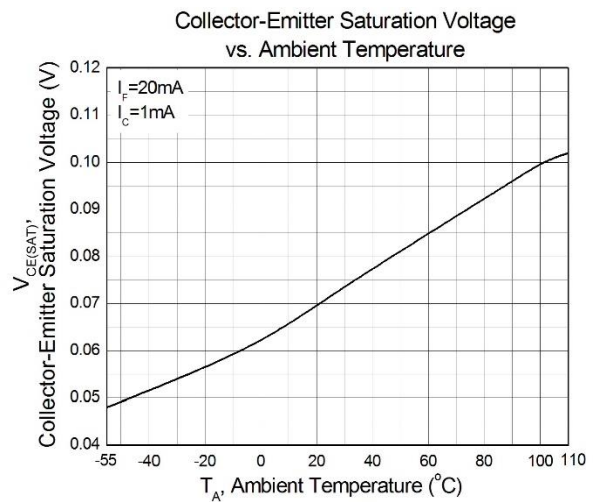
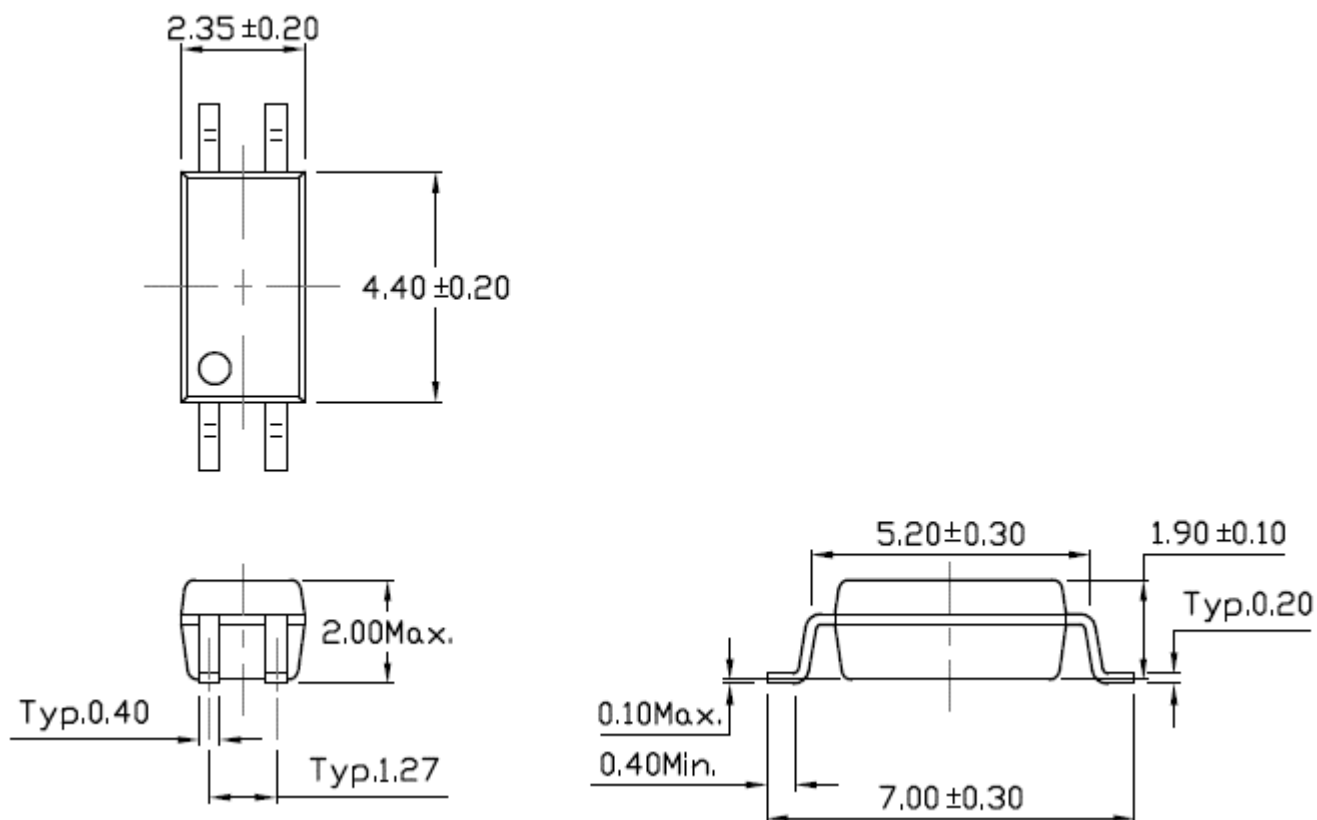


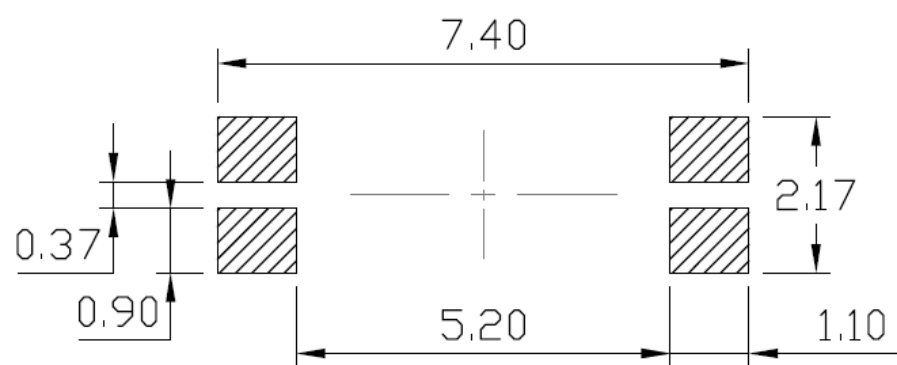
Figure 12



Package Dimension *Dimensions in mm unless otherwise stated*



Recommended Solder Mask *Dimensions in mm unless otherwise stated*





Marking Information



Note:

- CT : Denotes “CT Micro”
- 3H4 : Part Number
- X : “X” is CTR Rank (X= A, B, or none)
- V : VDE Safety Option (V or none)
- Y : Fiscal Year
- WW : Work Week
- K : Manufacturing Code

Ordering Information

CT3H4X(V)(Y)

- CT : Denotes “CT Micro”
- 3H4 : Part Number
- X : “X” is CTR Rank (X= A, B, or none)
- V : VDE Safety Option (V or none)
- Y : Tape and reel option (T1 or T2)

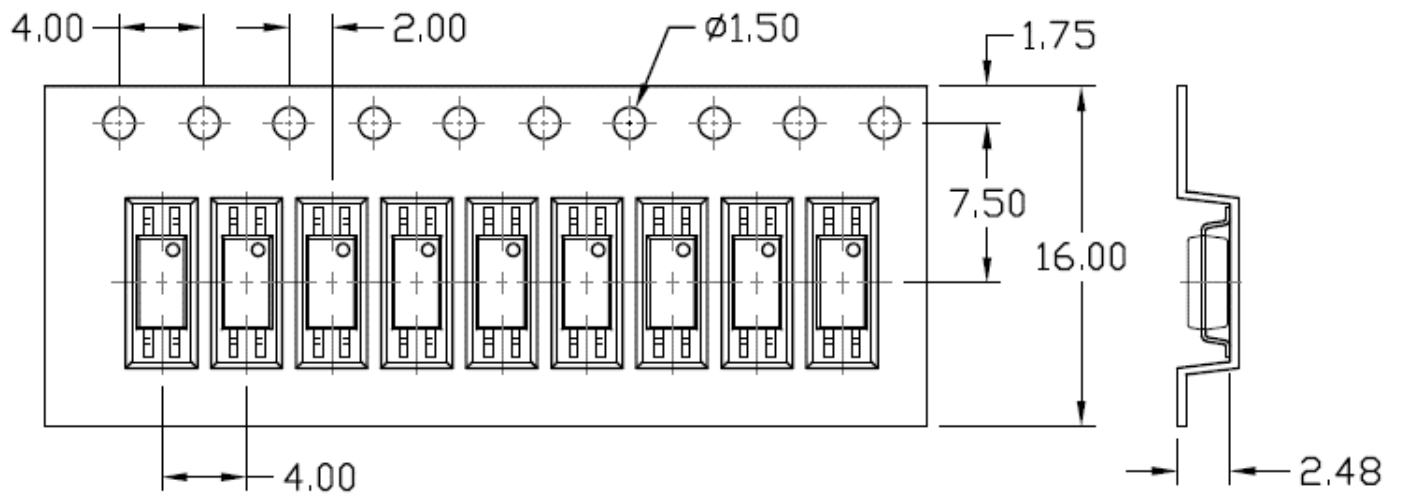
Option	Description	Quantity
T1	Surface Mount Lead Forming – With Option 1 Taping	5000 Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Taping	5000 Units/Reel



Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

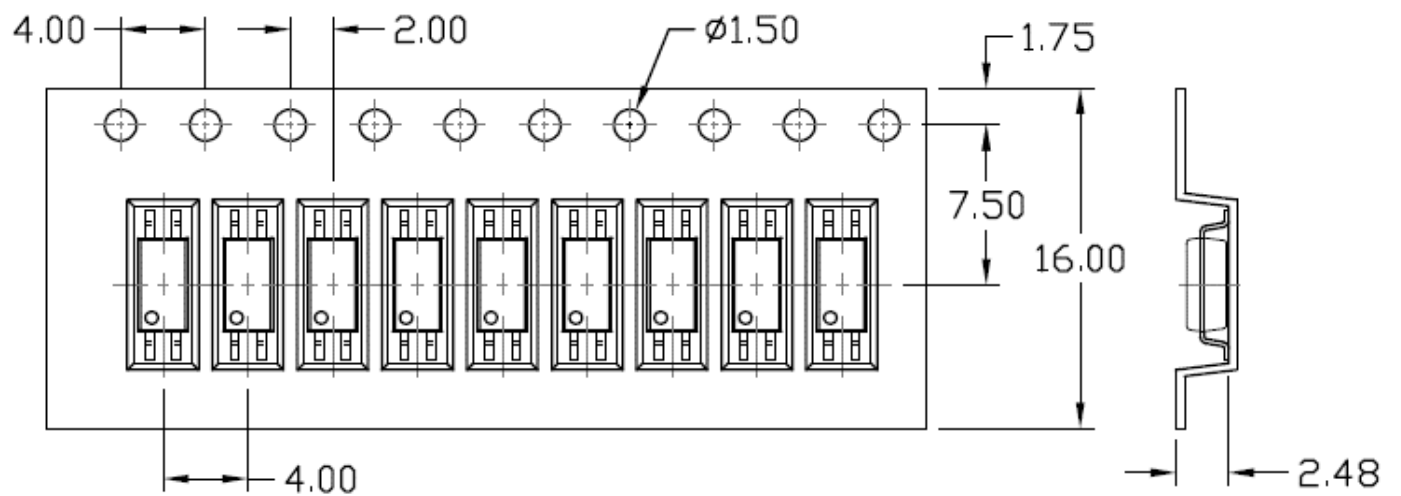
Option T1

Input Direction
→



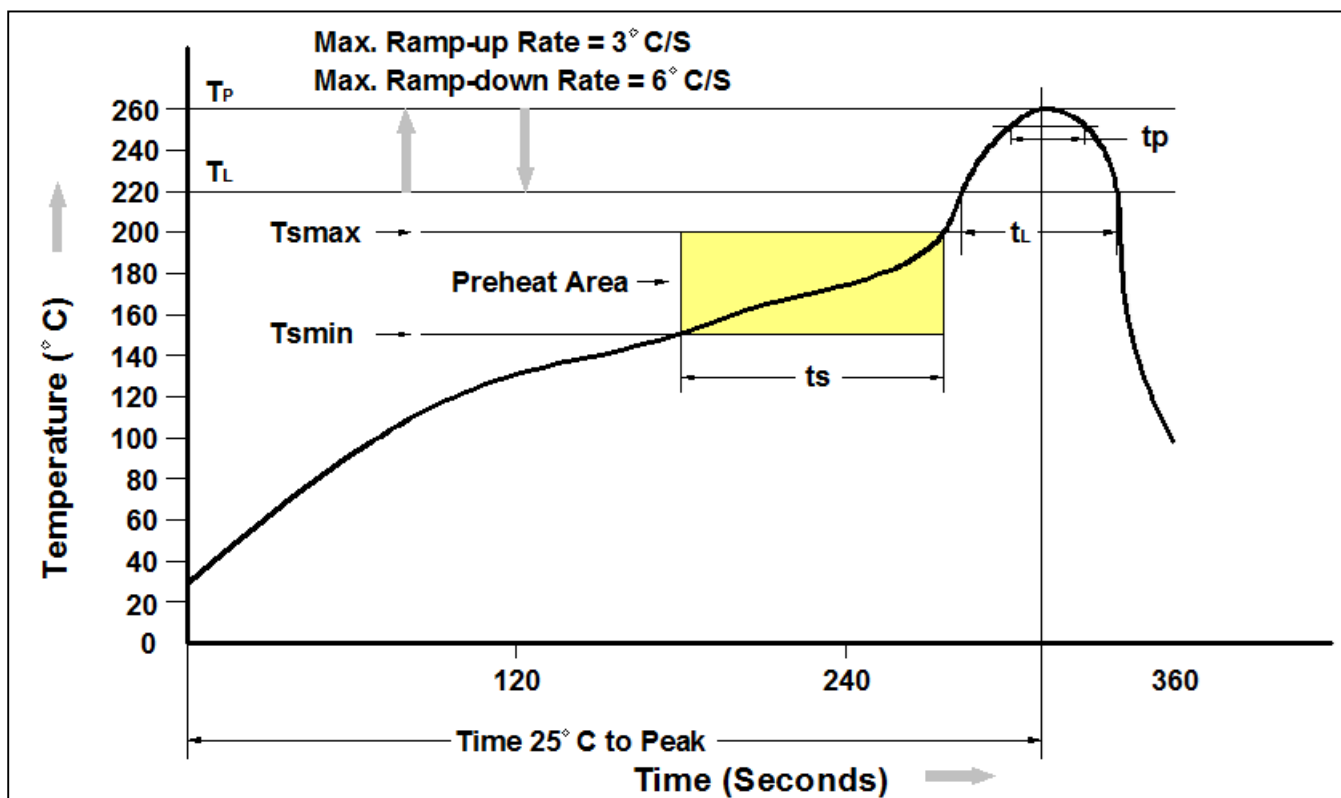
Option T2

Input Direction
→





Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{sm})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{sm} to T _{smax})	60-120 seconds
Ramp-up Rate (t _l to t _p)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _l) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _p) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



CT3H4 Series

4-Pin Half Pitch Mini-Flat Phototransistor

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